

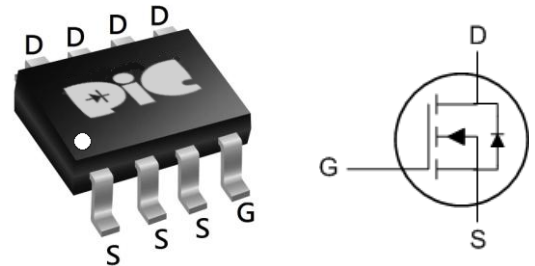
➤ General Description

This PAN30TJ16J N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

➤ SOP-8



➤ Application

- Notebook CPU Core-High-Side Switch

➤ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS} @ 10V^1$	$I_D @ T_A=25^\circ C$	15	A
Continuous Drain Current, $V_{GS} @ 10V^1$	$I_D @ T_A=70^\circ C$	12	A
Pulsed Drain Current ²	I_{DM}	75	A
Single Pulse Avalanche Energy ³	EAS	144.7	mJ
Avalanche Current	I_{AS}	53.8	A
Total Power Dissipation ⁴	$P_D @ T_A=25^\circ C$	1.5	W
Storage Temperature Range	T_{STG}	-55 to 175	$^\circ C$
Operating Junction Temperature Range	T_J	-55 to 175	$^\circ C$
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	85	$^\circ C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	24	$^\circ C/W$

➤ Electrical Characteristics ($T_J=25^\circ C$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
BVDSS Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^\circ C, I_D=1mA$	---	0.021	---	$V/^\circ C$
Static Drain-Source On-Resistance ²	$R_{DS(ON)}$	$V_{GS}=10V, I_D=15A$	---	---	4	m Ω
		$V_{GS}=4.5V, I_D=10A$	---	---	6	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	---	2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	-5.73	---	$mV/^\circ C$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ C$	---	---	5	
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
Forward Transconductance	g_{fs}	$V_{DS}=5V, I_D=15A$	---	26.5	---	S
Gate Resistance	R_g	$V_{DS}=10V, V_{GS}=0V, f=1MHz$	---	1.4	---	Ω
Total Gate Charge (4.5V)	Q_g	$V_{DS}=20V, V_{GS}=4.5V, I_D=12A$	---	31.6	---	nC
Gate-Source Charge	Q_{gs}		---	6.1	---	
Gate-Drain Charge	Q_{gd}		---	13.8	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=15V, V_{GS}=10V, R_G=1.5\Omega, I_D=15A$	---	11.2	---	ns
Rise Time	T_r		---	49	---	
Turn-Off Delay Time	$T_{d(off)}$		---	35	---	
Fall Time	T_f		---	7.8	---	
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	3075	---	pF
Output Capacitance	C_{oss}		---	400	---	
Reverse Transfer Capacitance	C_{rss}		---	315	---	

➤ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,5}	I_S	$V_G=V_D=0V, \text{Force Current}$	---	---	15	A
Pulsed Source Current ^{2,5}	I_{SM}		---	---	75	A
Diode Forward Voltage ²	V_{SD}	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1	V

Note :

- 1.Pulse width limited by maximum junction temperature.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=53.8A$
- 4.Ensure that the channel temperature does not exceed $150^\circ C$.
- 5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

➤ Typical Characteristics

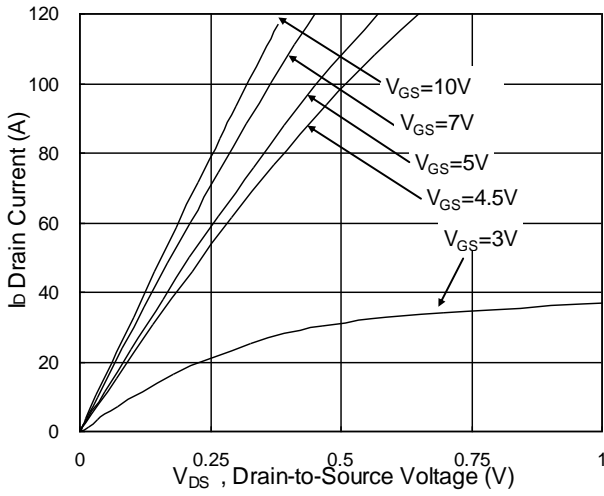


Fig.1 Typical Output Characteristics

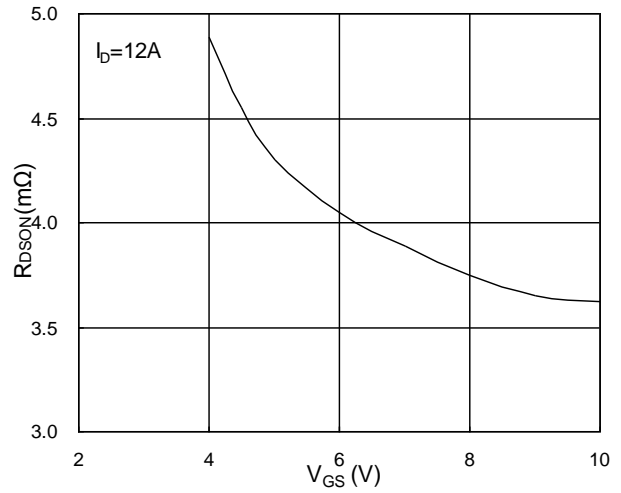


Fig.2 On-Resistance vs. G-S Voltage

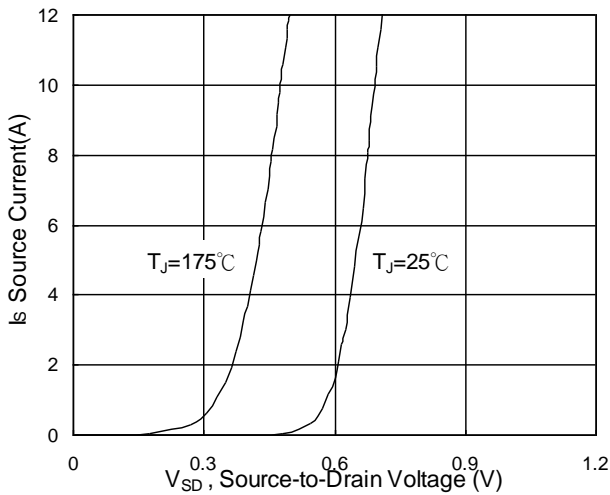


Fig.3 Forward Characteristics of Reverse

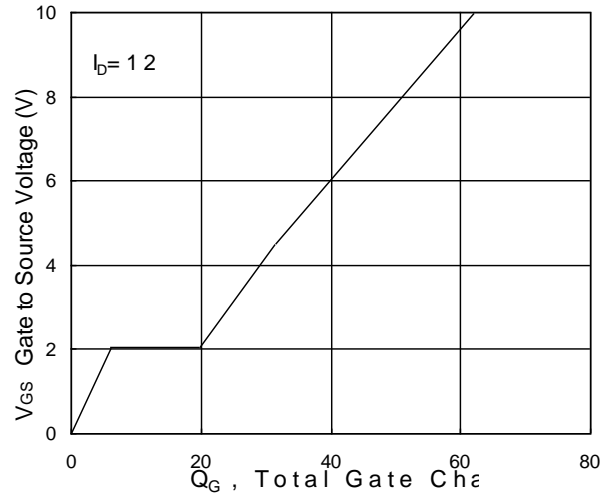


Fig.4 Gate-charge Characteristics

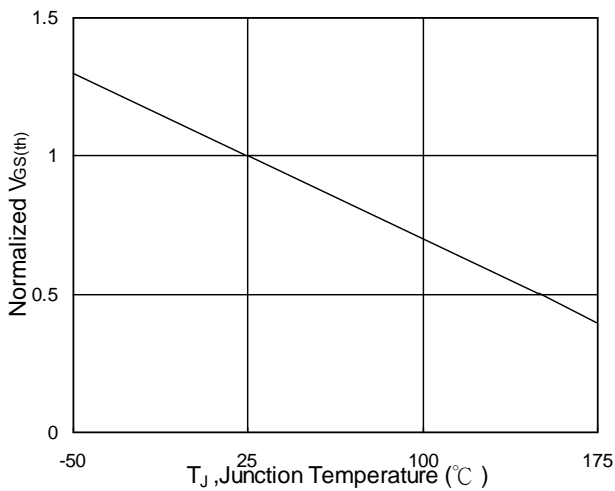


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

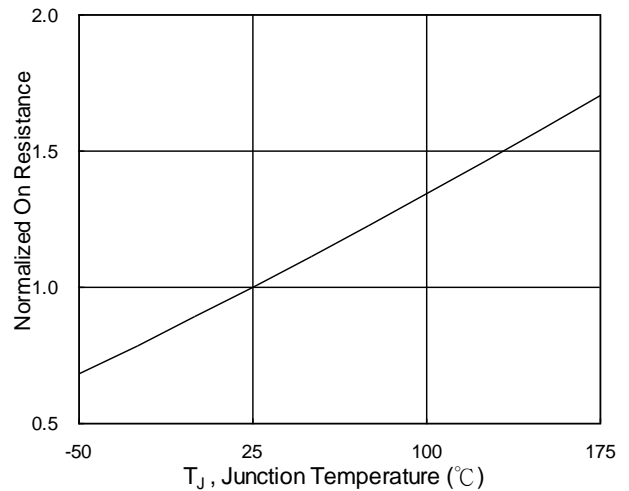


Fig.6 Normalized $R_{DS(ON)}$ vs. T_J

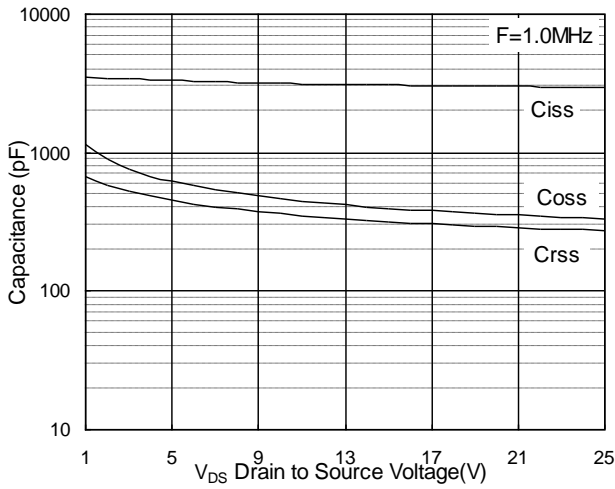


Fig.7 Capacitance

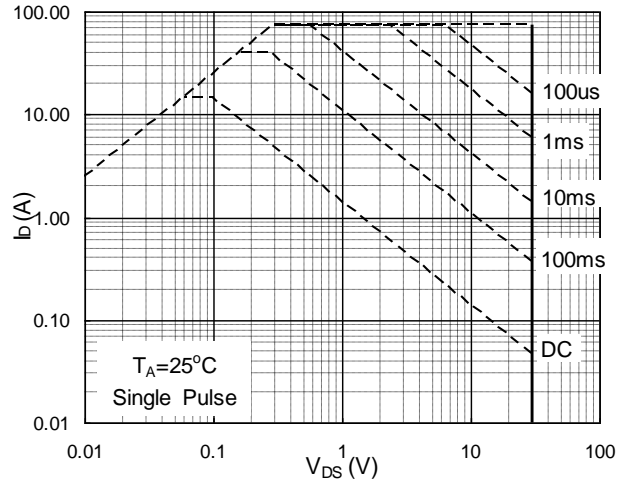


Fig.8 Safe Operating Area

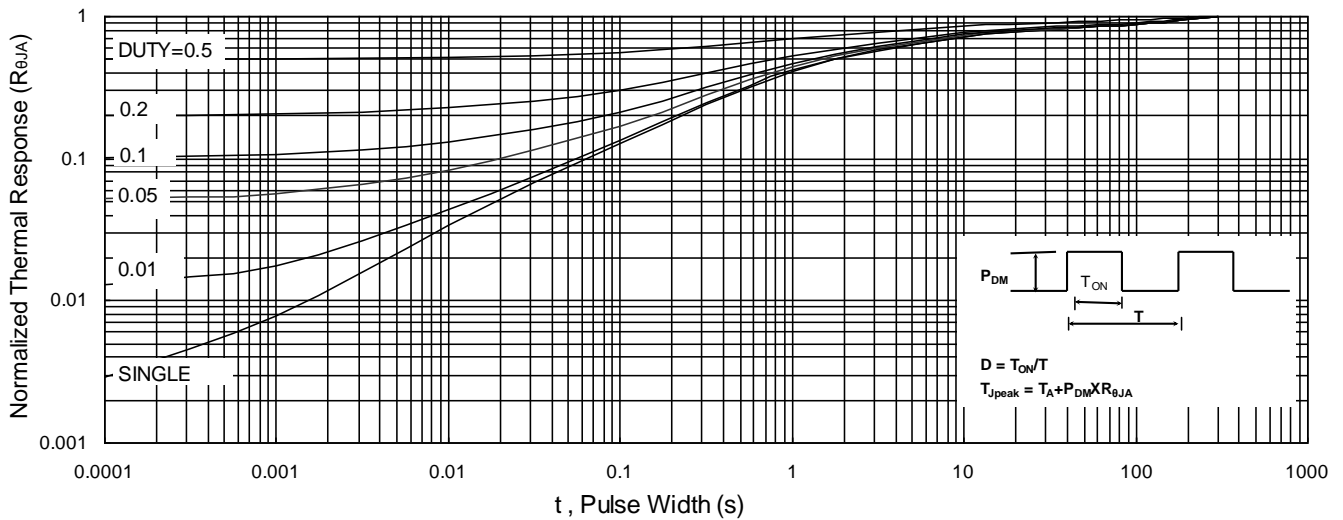


Fig.9 Normalized Maximum Transient Thermal Impedance

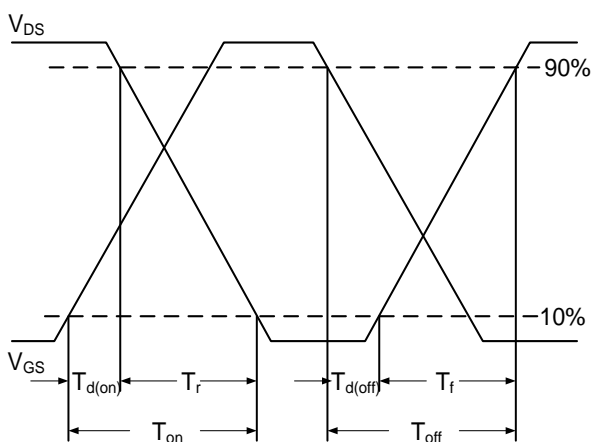


Fig.10 Switching Time Waveform

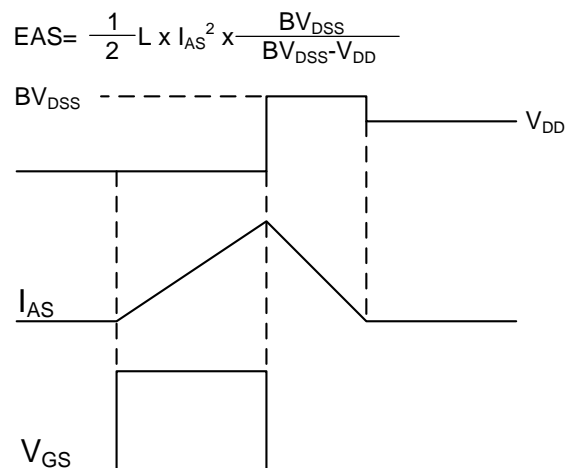
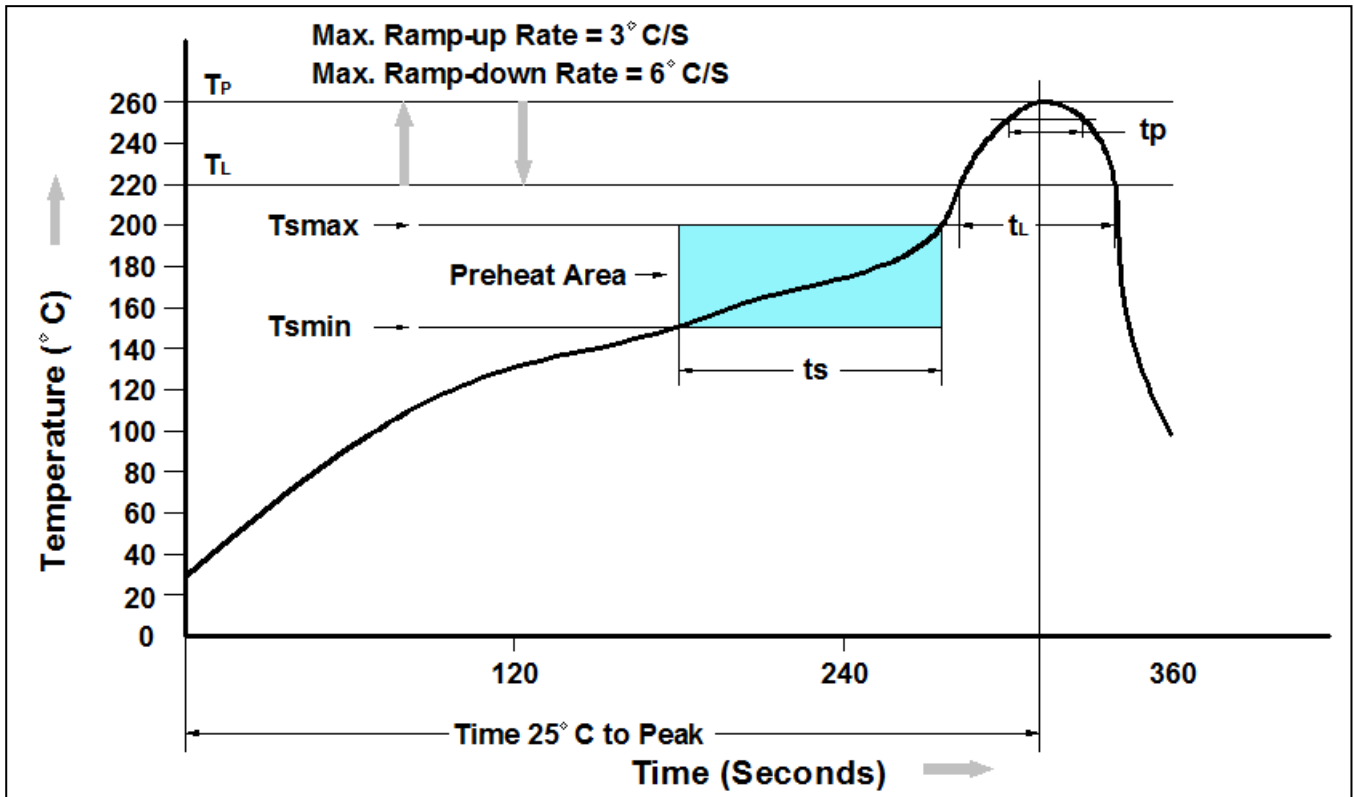


Fig.11 Unclamped Inductive Switching Waveform

➤ Recommend IR Reflow Soldering Thermal Profile

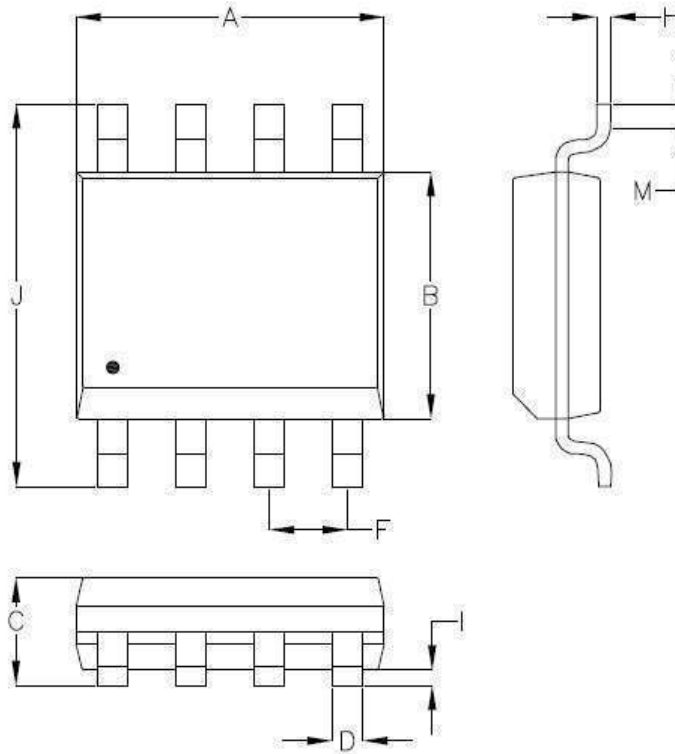


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T_{smin})	150°C
Temperature Max. (T_{smax})	200°C
Time (t_s) from (T_{smin} to T_{smax})	60-120 seconds
Average Ramp-up Rate (t_L to t_P)	3°C/second max.
Liquidous Temperature (T_L)	217°C
Time (t_L) Maintained Above (T_L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t_P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN30TJ16J	SOP-8 Reel	2500 pcs

➤ Package Information (SOP-8)



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.700	5.150	0.185	0.203
B	3.700	4.100	0.146	0.161
C	1.23	1.753	0.048	0.069
D	0.310	0.510	0.012	0.020
F	1.070	1.470	0.042	0.058
H	0.160	0.254	0.006	0.010
I	0.050	0.254	0.002	0.010
J	5.750	6.250	0.226	0.246
M	0.400	1.270	0.016	0.050

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